

## **ABSTRACT OF THE DISCLOSURE**

The present invention teaches an apparatus for pulling a single crystal, whereby a radial temperature gradient of a seed crystal and/or a neck is reduced to a minimum so as to inhibit occurrence of thermal stress and prevent induction of dislocations, thereby resulting in an improvement in dislocation-free rate of single crystals to be pulled in cases where a single crystal is pulled with a seed crystal and/or a neck being heated using an auxiliary heating device. The apparatus comprises a crucible to be charged with a melt, a heater located around the crucible, and an auxiliary heating device including a heating section which can be located so as to surround a seed crystal in a position near and above the melt, a transfer mechanism for withdrawing the heating section from a passing area of a single crystal, and a covering section to cover a clearance between the heating section and the seed crystal extending from the heating section.